





500V PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR POWERDI[®]5

Features and Benefits

- BV_{CEO} > -500V
- I_C = -150mA Continuous Collector Current
- 47% smaller than SOT223; 60% smaller than TO252 (D-PAK)
- Profile height just 1.1mm for thin application
- R_{0JA} efficient giving high P_D rating up to 2.8W
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free, "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

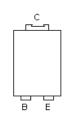
Mechanical Data

- Case: POWERDI[®]5
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.093 grams (approximate)

Applications

- Gate driver
- Startup switch in offline lighting
- Motor Control





Top View Pin-Out

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXTP560BP5-13	DXTP560B	13	16	5,000

Notes: 1. No purposefully added lead.

2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com

Marking Information



DXTP560B = Product Type Marking Code DII = Manufacturers' Code Marking K = Factory Designator YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 10 for 2010) WW = Week code (01 - 53)

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Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Limit	Unit
Collector-Base Voltage		V _{CBO}	-500	v
Collector-Emitter Voltage		V _{CEO}	-500	
Emitter-Base Voltage		V _{EBO}	-7	
Continuous Collector Current	(Note 4)	Ic -150		
Peak Pulse Current		I _{CM}	-500	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit			
	(Note 4)		2.8 22.4			
Power Dissipation Linear Derating Factor	(Note 5)	PD	1.3 10.4	-		
	(Note 6)		0.7 5.6			
Thermal Resistance, Junction to Ambient	(Note 4) (Note 5) (Note 6)	R _{0JA}	45 96 179	°C/W		
Thermal Resistance, Junction to Lead	(Note 7)	$R_{ ext{ heta}JL}$	14	°C/W		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C			

Notes: 4. For a device surface mounted on 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.

Same as note (4), except the device is mounted on 25mm x 25mm 1oz copper.

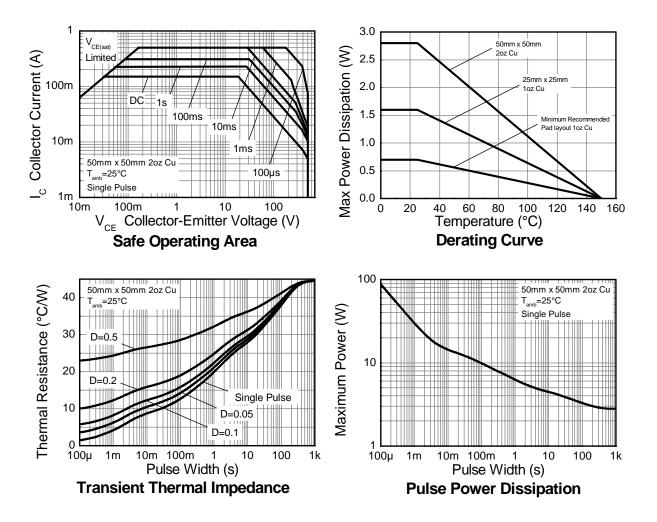
6. Same as note (4), except the device is mounted on a minimum recommended pad layout of 1oz copper.

7. Thermal resistance from junction to solder-point (at the end of the collector lead).





Thermal Characteristics





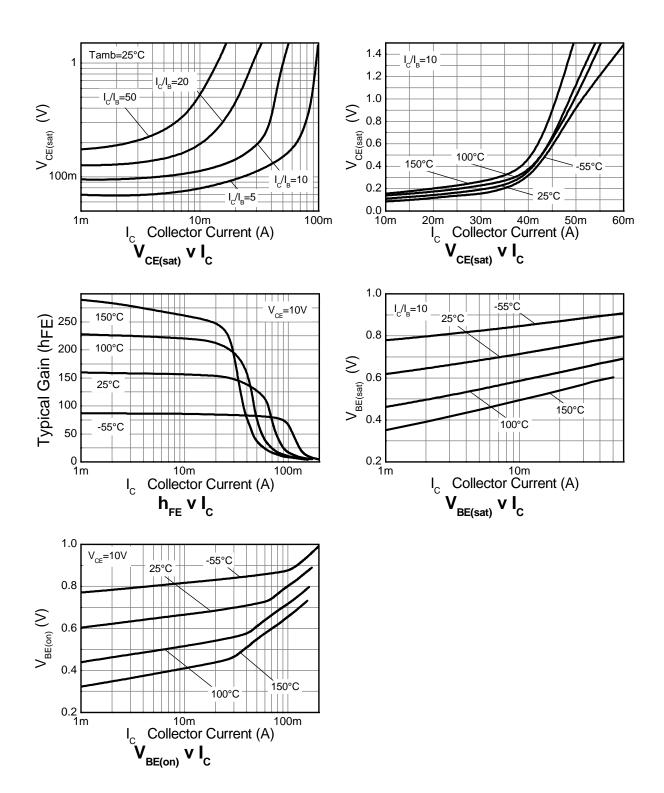
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		-500	_		V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 8)		-500		_	V	I _C = -10mA
Emitter-Base Breakdown Voltage		-7		_	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	_		-100	nA	V _{CB} = -500V
Collector Cutoff Current	ICES	_		-100	nA	V _{CE} = -500V
Emitter Cutoff Current	I _{EBO}	_		-100	nA	V _{EB} = -5.6V
Collector-Emitter Saturation Voltage (Note 8)		_		-200	mV	I _C = -20mA, I _B = -2mA
	V _{CE(sat)}			-500	mv	$I_{C} = -50 \text{mA}, I_{B} = -10 \text{mA}$
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}			-900	mV	I _C = -50mA, I _B = -10mA
Base-Emitter Turn-On Voltage (Note 8)	V _{BE(on)}			-900	mV	$V_{CE} = -10V, I_{C} = -50mA$
		100		300		$V_{CE} = -10V, I_{C} = -1mA$
DC Current Gain (Note 8)	h _{FE}	80		300		$V_{CE} = -10V, I_{C} = -50mA$
			15	—		$V_{CE} = -10V, I_C = -100mA$
Transition Frequency	f⊤	60	—	—	MHz	$V_{CE} = -20V, I_C = -10mA,$ f = 50MHz
Output Capacitance	C _{obo}	_		8	pF	$V_{CB} = -20V, f = 1MHz$
Switching Times	t _{on}	_	110	_	ns	$V_{CC} = -100V, I_{C} = -50mA,$
	t _{off}		1500		115	$I_{B1} = 5mA, I_{B2} = -10mA$

Notes: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics

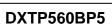


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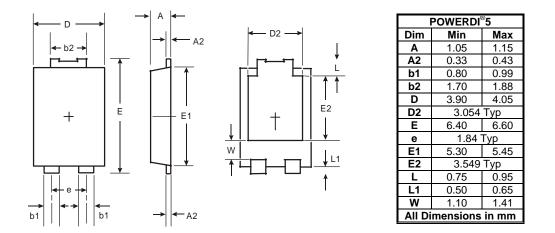
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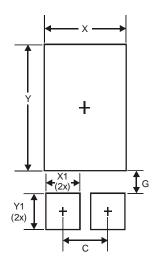




Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
С	1.840
G	0.852
Х	3.360
X1	1.390
Y	4.860
Y1	1.400



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